Silicon NPN Power Transistors 2N6465 2N6466

DESCRIPTION

·With TO-66 package
·Excellent safe operating area
·Complement to type 2N6467 2N6468

APPLICATIONS

·For use in audio amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N6465	Open emitter	110	V
		2N6466		130	
V_{CEO}	Collector-emitter voltage	2N6465	Open base	100	V
		2N6466		120	
V_{EBO}	Emitter-base voltage		Open collector	5	V
I_C	Collector current			4	A
P_D	Total power dissipation		T_C=25□	40	W
T_j	Junction temperature			150	□
T_{stg}	Storage temperature			-65~150	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}c}$	Thermal resistance junction to case	2.5	□/W

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	2N6465	I_C=50mA ;I_B=0	100			V
		2N6466		120			
V_{CEsat}	Collector-emitter saturation voltage		I_C=1.5A; I_B=0.15A			1.2	V
V_{BE}	Base-emitter on voltage		I_C=1.5A ; V_{CE}=4V			1.5	V
I_{CBO}	Collector cut-off current	2N6465	V_{CB}=110V; I_E=0			10	μA
		2N6466	V_{CB}=130V; I_E=0				
I_{CEO}	Collector cut-off current	2N6465	V_{CE}= 100V,I_B=0			100	μA
		2N6466	V_{CE}= 120V,I_B=0				
I_{EBO}	Emitter cut-off current		V_{EB}=5V; I_C=0			10	μA
h_{FE}	DC current gain		I_C=1.5A ; V_{CE}=4V	15		150	
f_T	Transition frequency		I_C=0.5A ; V_{CE}=10V	5			MHz

PACKAGE OUTLINE

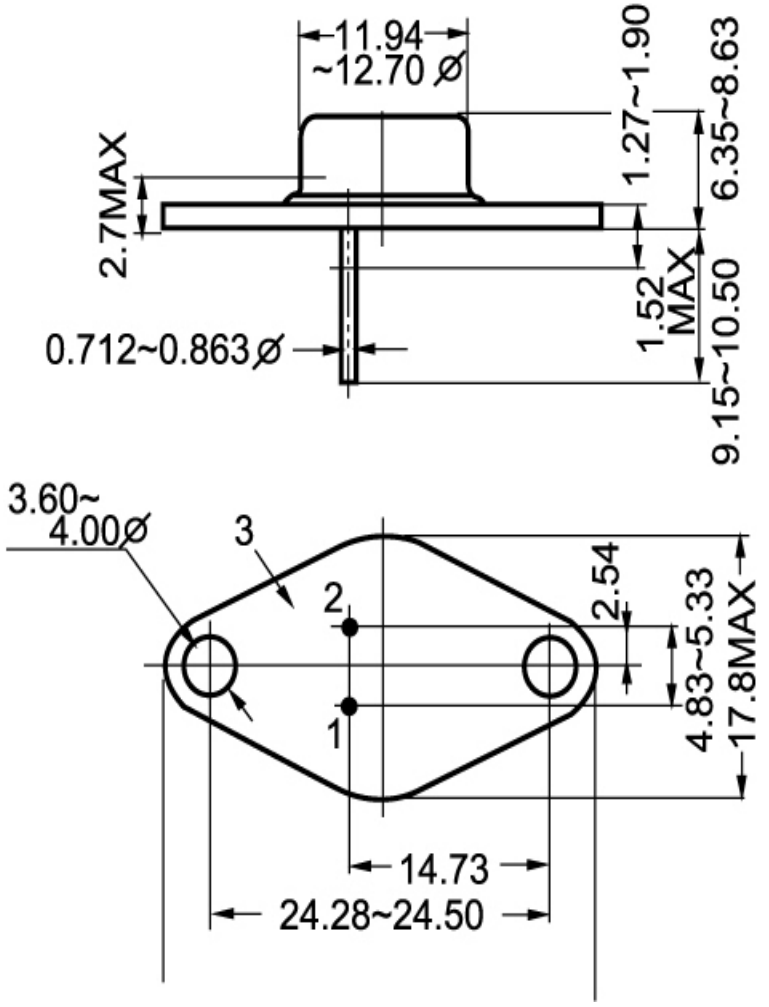

Fig.2 outline dimensions